

second MISFETs arranged in said second portion, said second MISFETs each having a gate electrode and a source and a drain region;

an insulating film formed over said first and second MISFETs;

a plurality of conductor plugs formed in said insulating film in said first and second portions;

a first conductive strip formed on said insulating film in said first portion and electrically connected to one of a source and a drain region of said first MISFETs by said conductor plugs; and

a second conductive strip formed on said insulating film in said second portion and electrically connected to one of a source and a drain region of said second MISFETs by said conductor plugs.

19. A semiconductor integrated circuit device according to claim 18, wherein each of said conductor plugs comprises a tungsten film.

20. A semiconductor integrated circuit device according to claim 18, wherein each of said conductor plugs comprises a multiplayer film of titanium nitride and tungsten.

21. A semiconductor integrated circuit device according to claim 18, wherein said first MISFETs comprise n-channel

MISFETs and said second MISFETs comprise a n-channel MISFET and a p-channel MISFET.

22. A semiconductor Integrated circuit device having a first portion for a memory array and a second portion for a circuit other than the memory array comprising:

first semiconductor regions arranged in said first portion of a semiconductor substrate;

second semiconductor regions arranged in said second portion of said semiconductor substrate;

a first insulating film formed over said semiconductor substrate;

a plurality of conductor plugs formed in said first insulating film in said first and second portions;

a first conductive strip formed on said first insulating film in said first portion and electrically connected to said first semiconductor regions by said conductor plugs; and

a second conductive strip formed on said first insulating film in said second portion and electrically connected to said second semiconductor regions by said conductor plugs.

23. A semiconductor integrated circuit device according to claim 22, wherein each of said conductor plugs comprises a tungsten film.

24. A semiconductor integrated circuit device according to claim 22, wherein each of said conductor plugs comprises a multiplayer film of titanium nitride and tungsten.

25. A semiconductor integrated circuit device according to claim 22, further comprising a second insulating film formed in said semiconductor substrate, wherein said first and second semiconductor regions touch said second insulating film.

26. A semiconductor integrated circuit device having a first portion for a memory array and a second portion for a circuit other than the memory array comprising:

a first MISFET arranged in said first portion, said first MISFET having a gate electrode and a source and a drain region formed in a semiconductor substrate;

a second MISFET arranged in said second portion, said second MISFET having a gate electrode and a source and a drain region formed in said semiconductor substrate;

a first insulating film formed over said first and second MISFETs;

a plurality of conductor plugs formed in said first insulating film in said first and second portions;

a first conductive strip formed over said first insulating film in said first portion and electrically connected to one of said source and drain regions of said

first MISFET by one of said conductor plugs;

a second conductive strip formed over said first insulating film in said first portion and electrically connected to the other of said source and drain regions of said first MISFET by one of said conductor plugs; and

a third conductive strip formed over said first insulating film in said second portion and electrically connected to one of said source and drain regions of said second MISFET by said conductor plugs; and

a fourth conductive strip formed over said first insulating film in said second portion and electrically connected to the other of said source and drain regions of said second MISFET by one of said conductor plugs.

27. A semiconductor integrated circuit device according to claim 26, wherein each of said conductor plugs comprises a tungsten film.

28. A semiconductor integrated circuit device according to claim 26, wherein each of said conductor plugs comprises a multiplayer film of titanium nitride and tungsten.

29. A semiconductor integrated circuit device according to claim 26, comprising a plurality of said first MISFETs and a plurality of said second MISFETs, wherein said first MISFETs comprise n-channel MISFETs and said second MISFETs comprise a

n-channel MISFET and a p-channel MISFET.

30. A semiconductor integrated circuit device according to claim 29, further comprising a second insulating film surrounding said first and second MISFETs.

31. A semiconductor integrated circuit device according to claim 30, further comprising a third insulating film formed on said first conductive strip, wherein said second conductive strip is formed on said third insulating film.

32. A semiconductor integrated circuit device having a first portion for a memory array and a second portion for a circuit other than the memory array comprising:

first semiconductor regions arranged in said first portion of a semiconductor substrate;

second semiconductor regions arranged in said second portion of said semiconductor substrate;

a plurality of conductor plugs formed on said first semiconductor regions and said second semiconductor regions;

a first insulating film formed over said semiconductor substrate and surrounding each of said conductor plugs;

a first conductive strip formed on said first insulating film and connected to said conductor plugs in said first portion; and

a second conductive strip formed on said first insulating film and connected to said conductor plugs in said second portion.

33. A semiconductor integrated circuit device according to claim 32, wherein each of said conductor plugs comprises a tungsten film,

34. A semiconductor integrated circuit device according to claim 32, wherein each of said conductor plugs comprises a multiplayer film of titanium nitride and tungsten.

35. A semiconductor integrated circuit device according to claim 33, further comprising a second insulating film formed in said semiconductor substrate, wherein said first and second semiconductor regions touch said second insulating film.

36. A semiconductor Integrated circuit device according to claim 34, wherein said second semiconductor regions include a p-type semiconductor region and an n-type semiconductor region.

37. A semiconductor integrated circuit device having a first portion for a memory array and
a second portion for a circuit other than the memory

array on a semiconductor substrate comprising:

a MISFET arranged in said first portion, said MISFET having first semiconductor regions and a gate electrode between said first semiconductor regions;

second semiconductor regions arranged in said second portion;

a plurality of first conductor plugs formed on said first semiconductor regions in said first portion and on said second semiconductor regions in said second portion;

a first insulating film formed over said semiconductor substrate and said first insulating film surrounding each of said first conductor plugs;

a first conductive strip formed on said first insulating film in said first portion and electrically connected to one of first semiconductor regions of said MISFET through one of said first conductor plugs; and

a second conductive strip formed on said first insulating film in said second portion and electrically connected to said second semiconductor regions through said first conductor plugs;

a second conductor plug formed on said first conductor plug connected to the other of said first semiconductor regions;

a second insulating film surrounding said second conductor plug; and a third conductive strip formed on said second insulating film and electrically connected to said